

P-Channel 20 V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
- 20	0.108 at $V_{GS} = -4.5$ V	- 4.1	4 nC
	0.175 at $V_{GS} = -2.5$ V	- 3.3	

SCHOTTKY PRODUCT SUMMARY

V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A) ^a
30	0.5 at 1 A	2

FEATURES

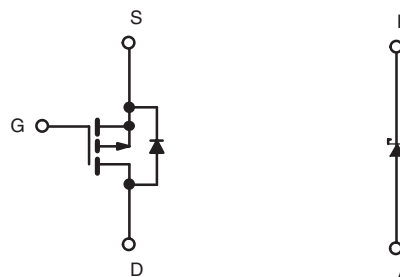
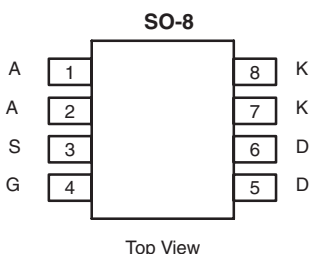
- Halogen-free According to IEC 61249-2-21 Definition
- LITTLE FOOT® Plus Schottky
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Portable Devices
- Ideal for Boost Circuits
- Ideal for Buck Circuits



Ordering Information: Si4823DY-T1-E3 (Lead (Pb)-free)
Si4823DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage (MOSFET)	V_{DS}	- 20	V
Reverse Voltage (Schottky)	V_{KA}	30	
Gate-Source Voltage (MOSFET)	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) (MOSFET)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Pulsed Drain Current (MOSFET)	I_{DM}	- 15	A
Continuous Source-Drain Diode Current (MOSFET Diode Conduction)	I_S	- 2.3	
		- 1.4 ^{b, c}	
Average Forward Current (Schottky)	I_F	- 2 ^b	A
Pulsed Forward Current (MOSFET)	I_{FM}	- 3	
Maximum Power Dissipation (MOSFET)	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Maximum Power Dissipation (Schottky)	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^{b, e}	R_{thJA}	60	71.5	°C/W
Maximum Junction-to-Foot (Drain) (MOSFET)	R_{thJF}	35	45	
Maximum Junction-to-Ambient (Schottky) ^{b, f}	R_{thJA}	63	78	
Maximum Junction-to-Foot (Drain) (Schottky)	R_{thJF}	39	47	

Notes:

- a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. $t = 10$ s.
d. Based on $T_C = 25$ °C.
e. Maximum under steady state conditions is 110 °C/W.
f. Maximum under steady state conditions is 115 °C/W.

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 20		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.6		- 1.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ 5 V, V _{GS} = - 4.5 V	- 15			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.3 A		0.090	0.108	Ω
		V _{GS} = - 2.5 V, I _D = - 2.6 A		0.140	0.175	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 3.3 A		6		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		330	660	pF
Output Capacitance	C _{oss}			80	160	
Reverse Transfer Capacitance	C _{rss}			57	114	
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 10 V, I _D = - 3.3 A		8	12	nC
		V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 3.3 A		4	6	
Q _{gs}			0.8			
Gate-Drain Charge	Q _{gd}			1.4		
Gate Resistance	R _g	f = 1 MHz	1.2	6	12	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 3.8 Ω I _D ≅ - 2.6 A, V _{GEN} = - 10 V, R _g = 1 Ω		3	6	ns
Rise Time	t _r			10	20	
Turn-Off DelayTime	t _{d(off)}			16	24	
Fall Time	t _f			8	15	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 3.8 Ω I _D ≅ - 2.6 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		18	27	
Rise Time	t _r			40	60	
Turn-Off DelayTime	t _{d(off)}			18	27	
Fall Time	t _f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 6.2	A
Pulse Diode Forward Current	I _{SM}				- 15	
Body Diode Voltage	V _{SD}	I _S = - 2.6 A, V _{GS} = 0 V		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 2.6 A, dI/dt = 100 A/μs, T _J = 25 °C		23	35	ns
Body Diode Reverse Recovery Charge	Q _{rr}			14	21	nC
Reverse Recovery Fall Time	t _a			11		ns
Reverse Recovery Rise Time	t _b			12		

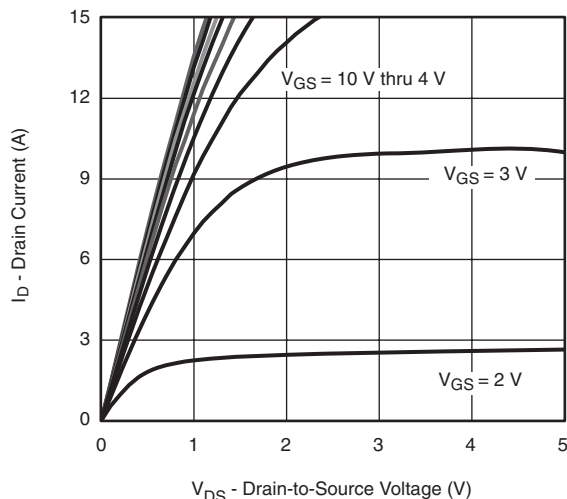
Notes:

- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

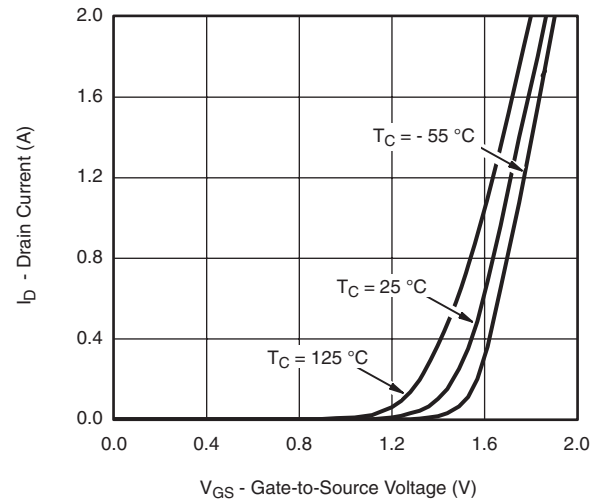
SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1\text{ A}$		0.46	0.50	V
		$I_F = 1\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.41	0.50	
Maximum Reverse Leakage Current	I_{rm}	$V_R = 30\text{ V}$		0.025	0.1	mA
		$V_R = 30\text{ V}, T_J = 85\text{ }^{\circ}\text{C}$		0.6	6	
		$V_R = 30\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$		5	25	
Junction Capacitance	C_T	$V_R = 15\text{ V}$		35		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

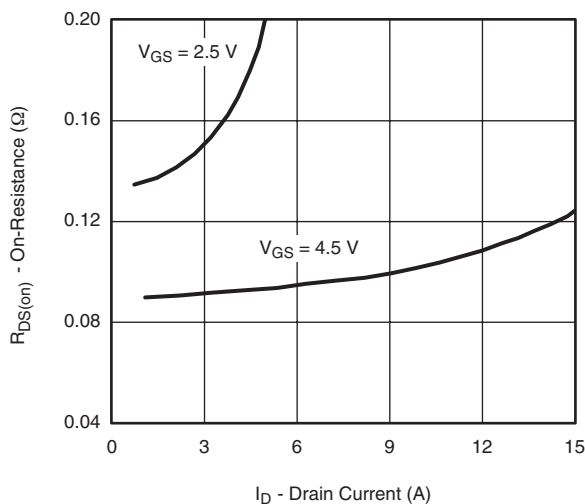
MOSFET TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted



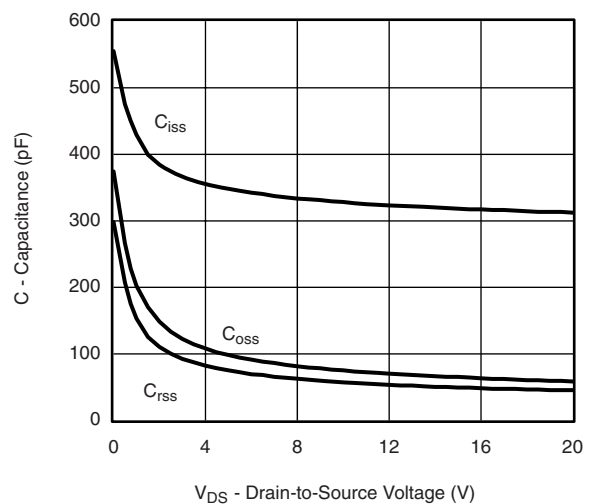
Output Characteristics



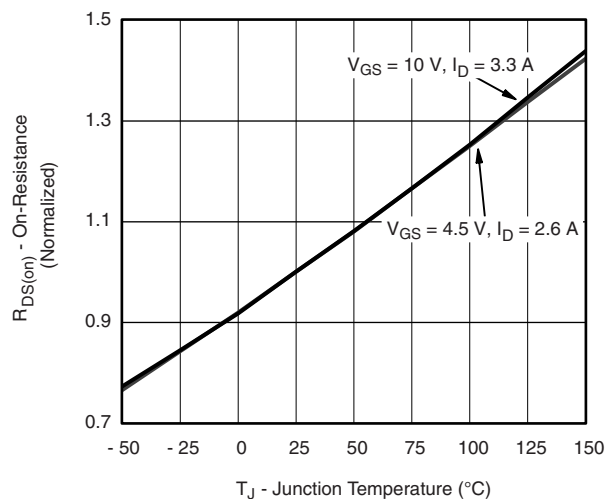
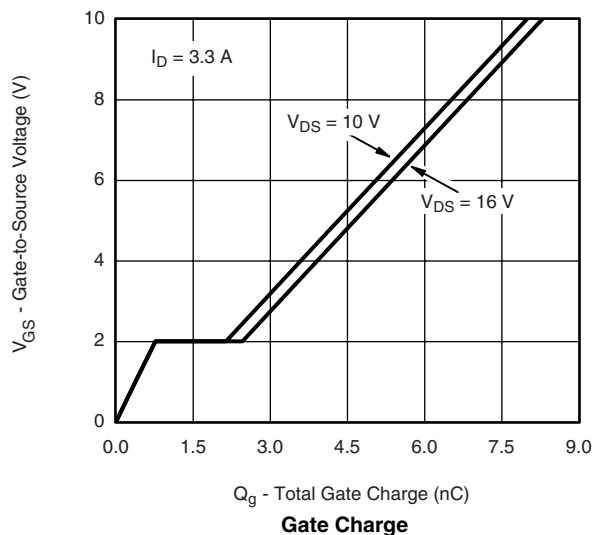
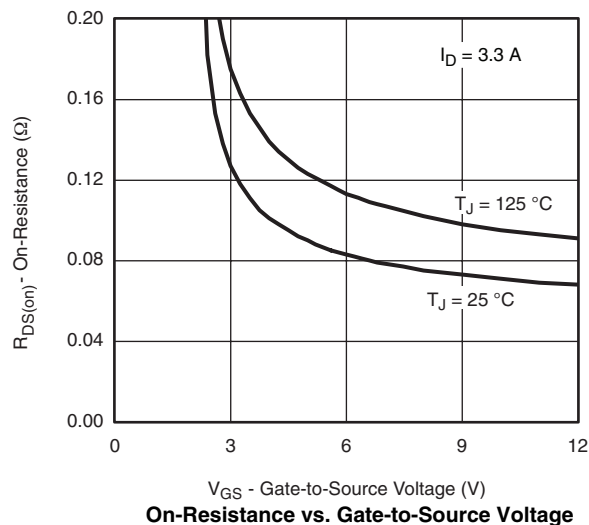
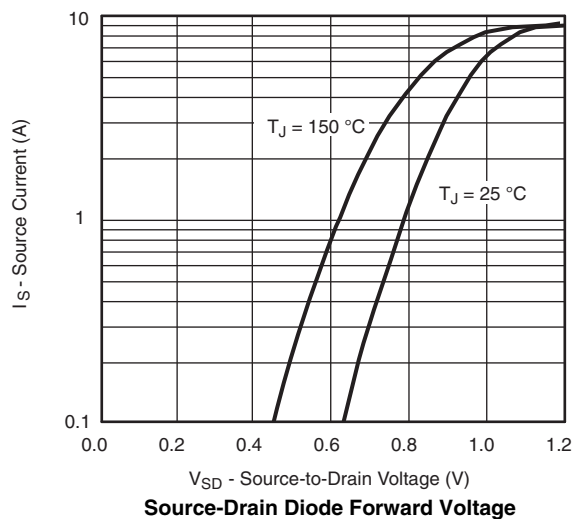
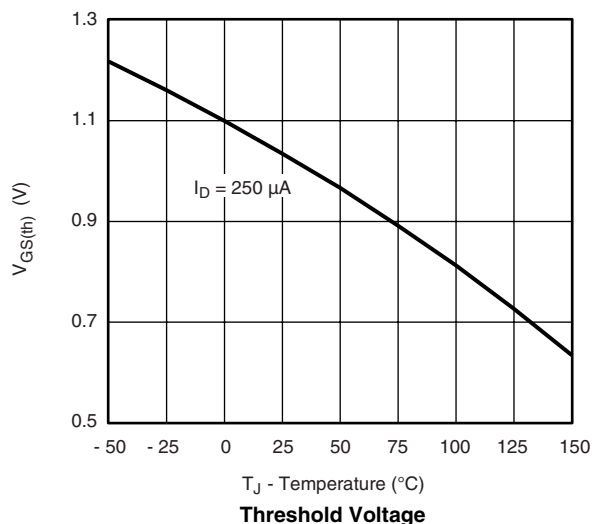
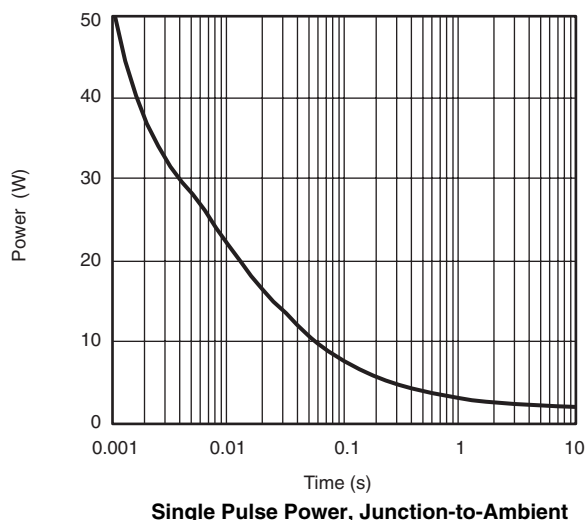
Transfer Characteristics



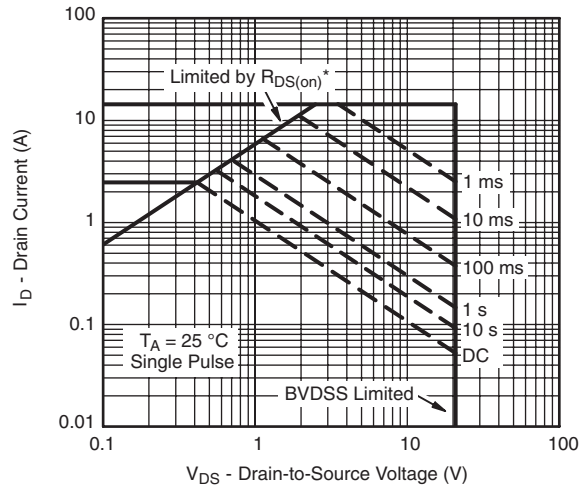
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

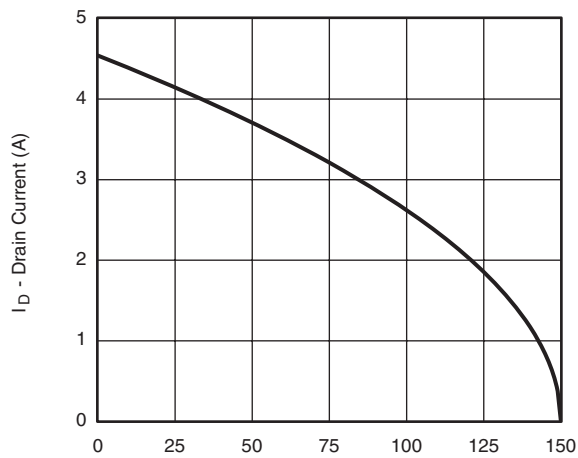
MOSFET TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted

On-Resistance vs. Junction Temperature

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient

MOSFET TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted



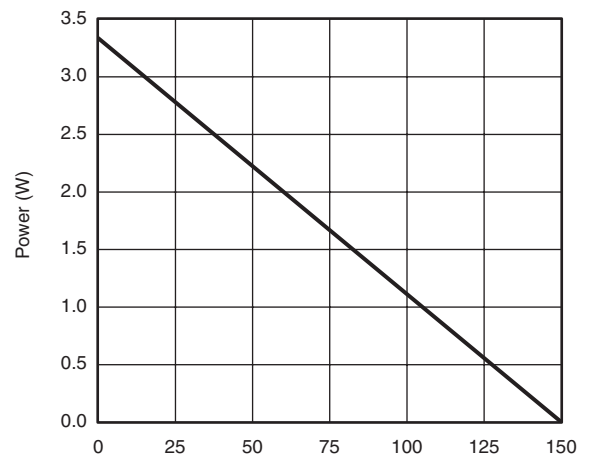
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



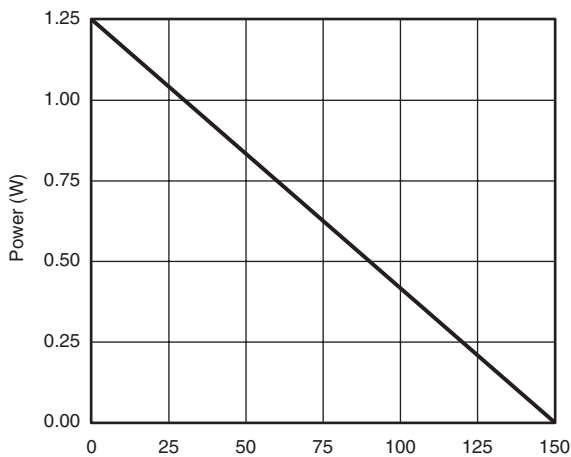
T_C - Case Temperature (°C)

Current Derating*



T_C - Case Temperature (°C)

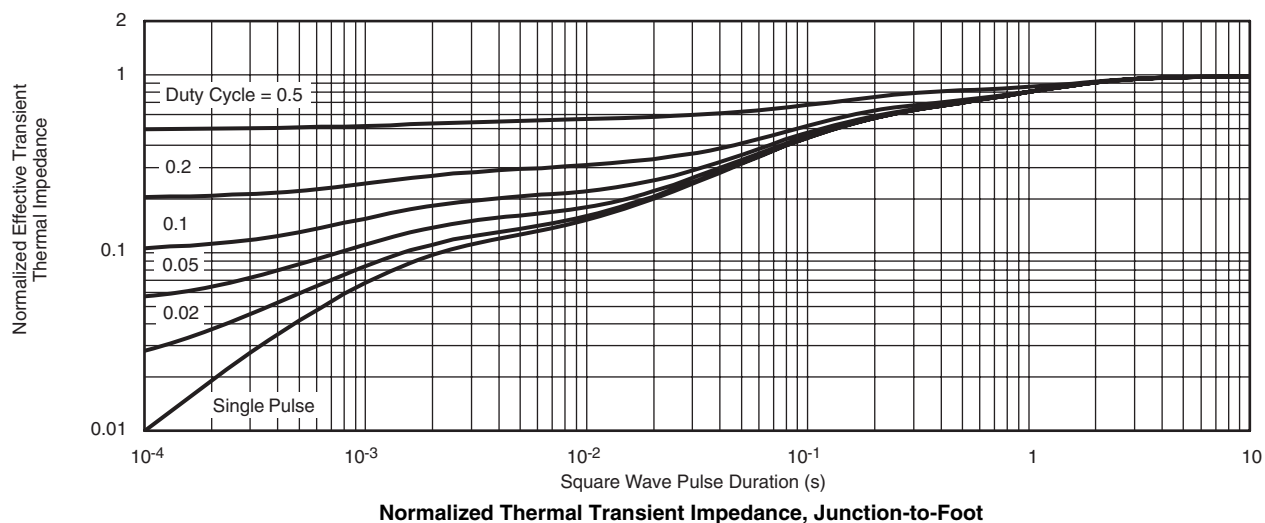
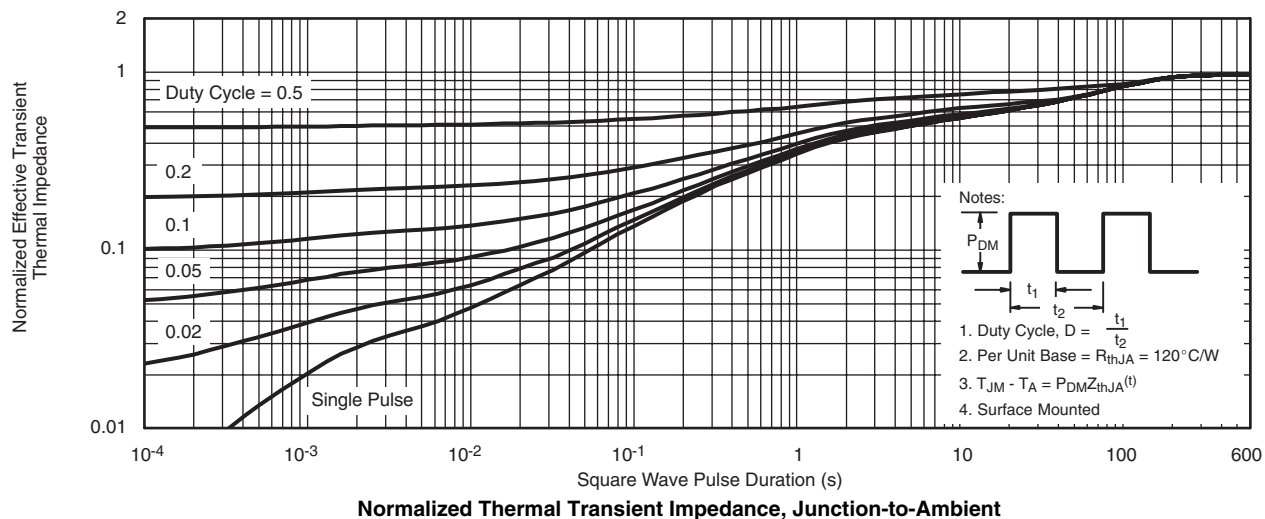
Power Derating, Junction-to-Case



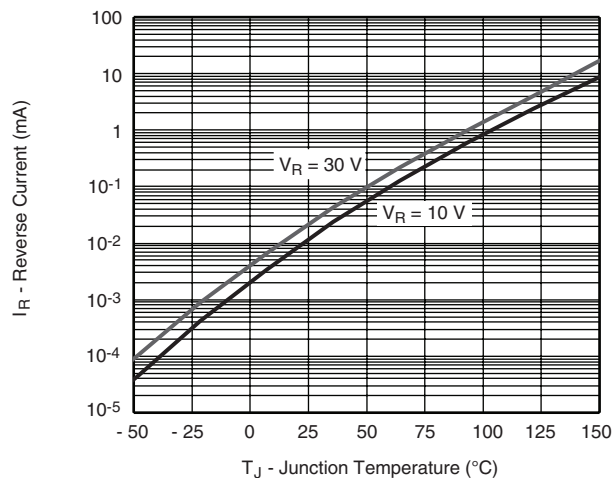
T_A - Ambient Temperature (°C)

Power Derating, Junction-to-Ambient

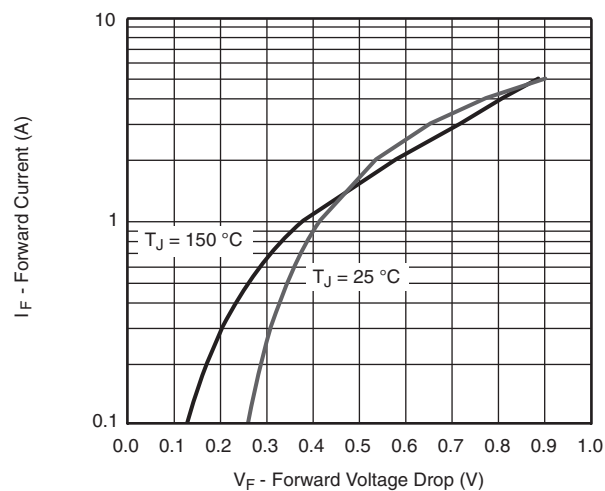
* The power dissipation P_D is based on $T_{J(max)} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

MOSFET TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted


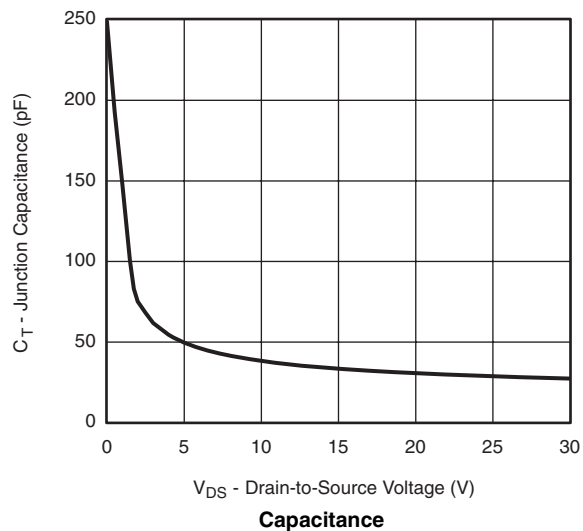
SCHOTTKY TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$, unless otherwise noted



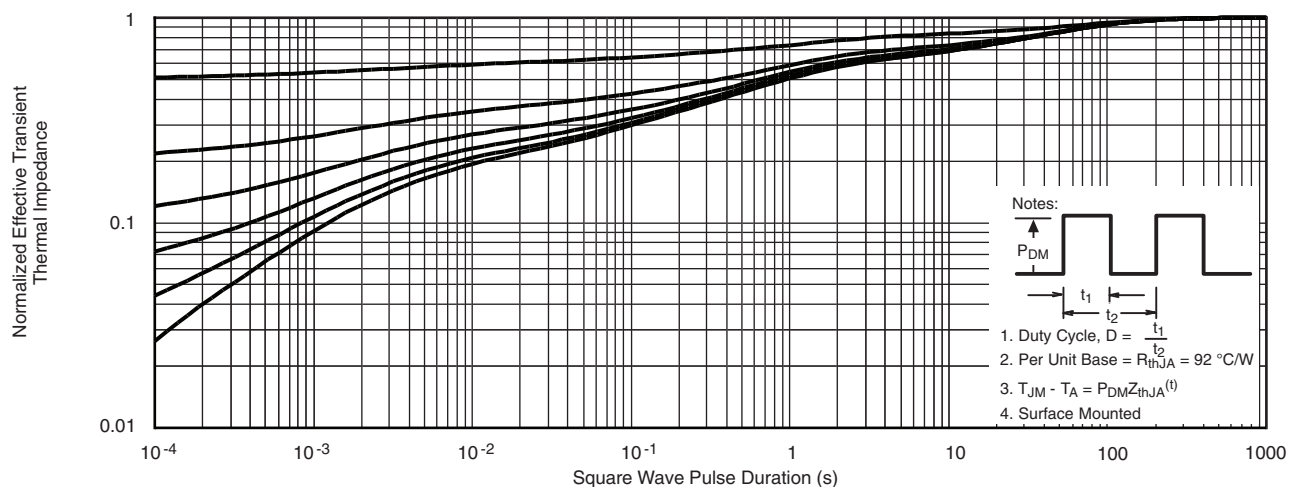
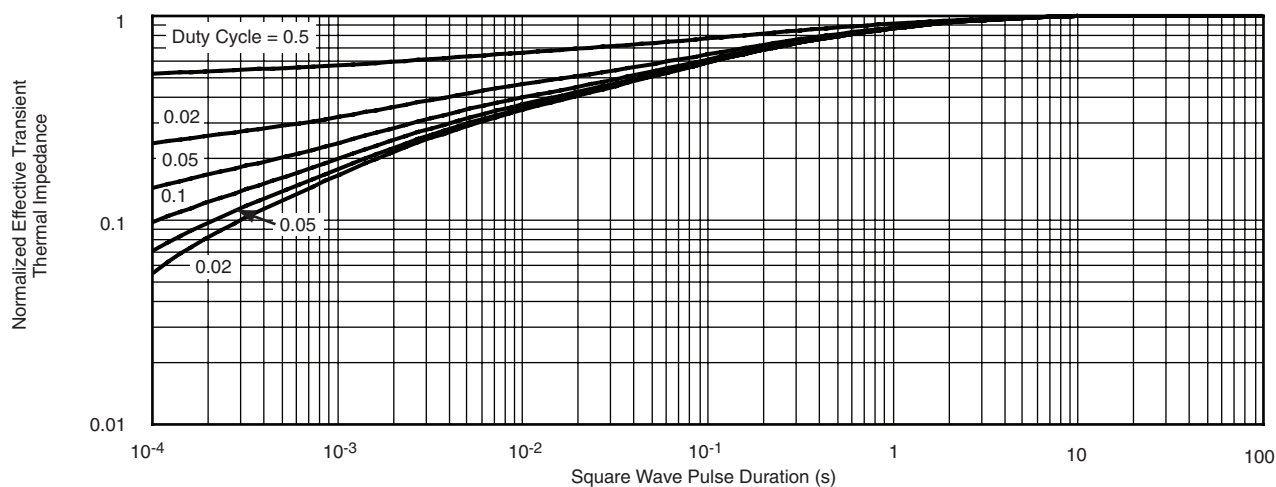
Reverse Current vs. Junction Temperature



Forward Voltage Drop



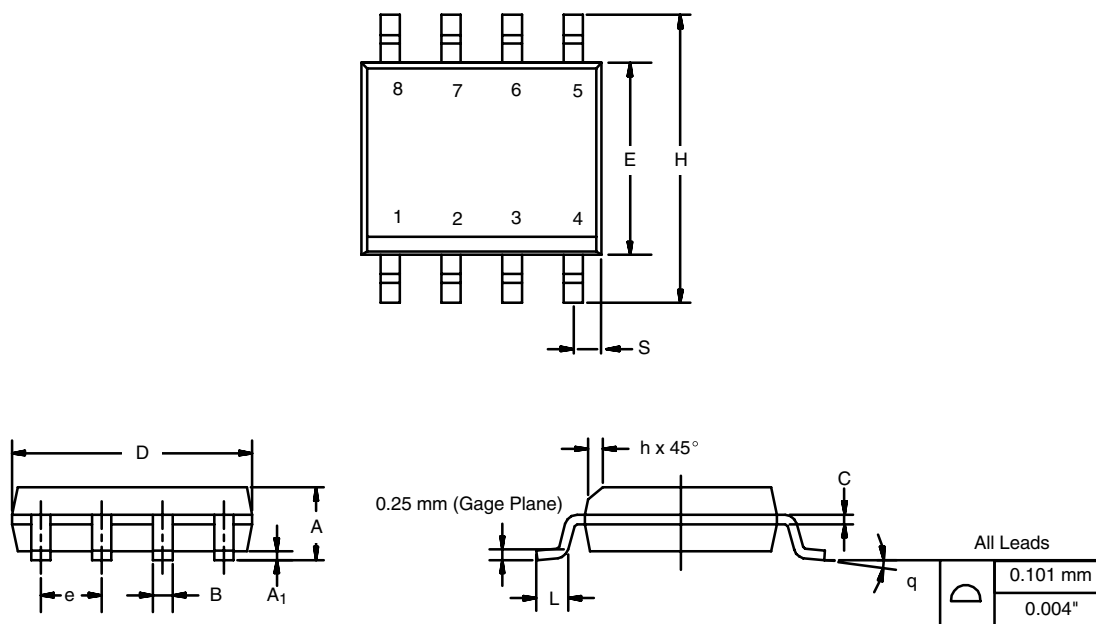
Capacitance

SCHOTTKY TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

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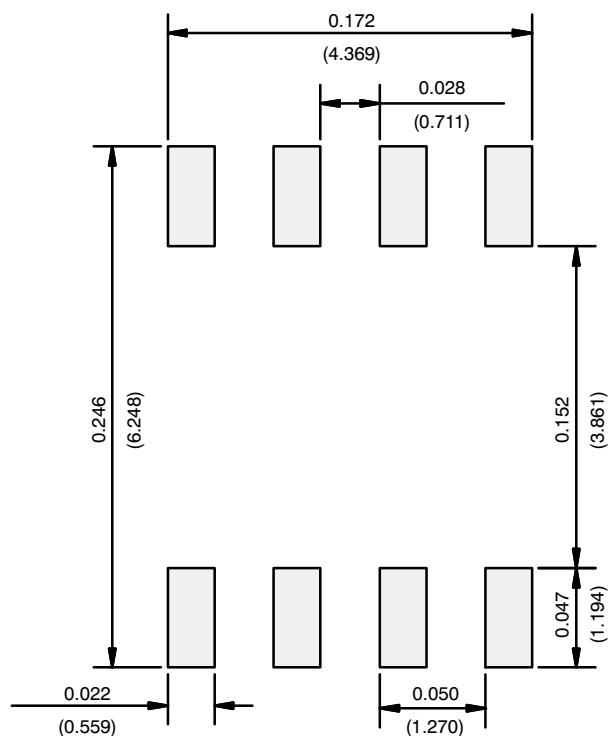
SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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